

Kazutoshi Kojima

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Carrier dynamics of silicon vacancies of SiC under simultaneous optically and electrically excitations. Applied Physics Letters, 2021, 118, .	3.3	4
2	Thermometric quantum sensor using excited state of silicon vacancy centers in 4H-SiC devices. Applied Physics Letters, 2021, 118, .	3.3	12
3	SiC p+n Junction Diodes Toward Beam Monitor Applications. IEEE Transactions on Nuclear Science, 2021, 68, 2787-2793.	2.0	4
4	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. Journal of Applied Physics, 2020, 128, 105702.	2.5	7
5	Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. Materials, 2020, 13, 4818.	2.9	2
6	Development of 4H-SiC Schottky np diode with high blocking voltage and ultralow on-resistance. Applied Physics Letters, 2020, 116, .	3.3	9
7	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. Review of Scientific Instruments, 2020, 91, 123902.	1.3	8
8	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-n diodes. Japanese Journal of Applied Physics, 2018, 57, 04FR07.	1.5	28
9	Ammonia-free high temperature metalorganic vapor phase epitaxy (AFHT-MOVPE): a new approach to high quality AlN growth. CrystEngComm, 2018, 20, 7364-7370.	2.6	10
10	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. Journal of Crystal Growth, 2017, 476, 99-106.	1.5	4
11	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC p-n diodes. Applied Physics Express, 2017, 10, 081201.	2.4	17
12	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, P547-P552.	1.8	1
13	An empirical growth window concerning the input ratio of HCl/SiH ₄ gases in filling 4H-SiC trench by CVD. Applied Physics Express, 2017, 10, 055505.	2.4	14
14	Study of spiral growth on 4H-silicon carbide on-axis substrates. Journal of Crystal Growth, 2017, 475, 251-255.	1.5	5
15	Strong impact of slight trench direction misalignment from $[11\bar{1}0]$ on deep trench filling epitaxy for SiC super-junction devices. Japanese Journal of Applied Physics, 2017, 56, 04CR05.	1.5	21
16	Reduction of background carrier concentration and lifetime improvement for 4H-SiC C-face epitaxial growth. Japanese Journal of Applied Physics, 2017, 56, 081302.	1.5	4
17	Electrical and physical characterizations of the effects of oxynitridation and wet oxidation at the interface of SiO ₂ /4H-SiC(0001) and. Japanese Journal of Applied Physics, 2016, 55, 04ER19.	1.5	5
18	Numerical analysis of the Gibbs-Thomson effect on trench-filling epitaxial growth of 4H-SiC. Applied Physics Express, 2016, 9, 035601.	2.4	14

#	ARTICLE	IF	CITATIONS
19	Influence of growth pressure on filling 4H-SiC trenches by CVD method. Japanese Journal of Applied Physics, 2016, 55, 01AC04.	1.5	8
20	Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. Applied Physics Express, 2015, 8, 121302.	2.4	12
21	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. Nuclear Instruments & Methods in Physics Research B, 2015, 348, 240-245.	1.4	5
22	Filling 4H-SiC trench towards selective epitaxial growth by adding HCl to CVD process. Applied Physics Express, 2015, 8, 065502.	2.4	20
23	Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. Journal of Applied Physics, 2015, 118, .	2.5	13
24	Systematic investigation on in-plane anisotropy of surface and buried channel mobility of metal-oxide-semiconductor field-effect-transistors on Si-, a-, and m-face 4H-SiC. Applied Physics Letters, 2015, 106, .	3.3	12
25	Synchrotron X-ray topography analysis of local damage occurring during polishing of 4H-SiC wafers. Japanese Journal of Applied Physics, 2015, 54, 091301.	1.5	15
26	Experiment on alleviating the bending of CVD-grown heavily Al-doped 4H-SiC epiwafer by codoping of N. Japanese Journal of Applied Physics, 2015, 54, 04DP08.	1.5	9
27	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. Japanese Journal of Applied Physics, 2015, 54, 04DP04.	1.5	7
28	Suppression of 3C-Inclusion Formation during Growth of 4H-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. Materials, 2014, 7, 7010-7021.	2.9	7
29	Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. Materials Science Forum, 2014, 778-780, 125-130.	0.3	2
30	Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H ₂ -SiH ₄ -C ₃ H ₈ CVD System. Materials Science Forum, 2014, 778-780, 214-217.	0.3	5
31	Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm \uparrow Size SiC Epitaxial Wafer. Materials Science Forum, 2014, 778-780, 139-142.	0.3	0
32	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. Materials Science Forum, 2014, 778-780, 151-154.	0.3	3
33	Suppressing Al memory effect on CVD growth of 4H-SiC epilayers by adding hydrogen chloride gas. Japanese Journal of Applied Physics, 2014, 53, 04EP07.	1.5	2
34	Linear energy transfer dependence of single event gate rupture in SiC MOS capacitors. Nuclear Instruments & Methods in Physics Research B, 2014, 319, 75-78.	1.4	18
35	Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. Journal of Crystal Growth, 2014, 401, 673-676.	1.5	9
36	Defect-induced performance degradation of 4H-SiC Schottky barrier diode particle detectors. Journal of Applied Physics, 2013, 113, .	2.5	32

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37	The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 380, 85-92.	1.5	34
38	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 381, 139-143.	1.5	13
39	Effects of radiation-induced defects on the charge collection efficiency of a silicon carbide particle detector. , 2013, , .		0
40	Breakdown voltage in silicon carbide metal-oxide-semiconductor devices induced by ion beams. , 2013, , .		0
41	Electrical Properties of MOS Structures on 4H-SiC (11-20) Face. Materials Science Forum, 2013, 740-742, 621-624.	0.3	6
42	Reducing the Wafer Off Angle for 4H-SiC Homoepitaxy. ECS Transactions, 2013, 58, 111-117.	0.5	1
43	4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1°. ECS Journal of Solid State Science and Technology, 2013, 2, N3012-N3017.	1.8	16
44	Suppression of Al Memory-Effect on Growing 4H-SiC Epilayers by Hot-Wall Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2013, 52, 04CP04.	1.5	1
45	E_1 and E_2 traps in 6H-SiC studied with Laplace deep level transient spectroscopy. Applied Physics Letters, 2013, 102, .	3.3	12
46	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. Journal of Applied Physics, 2012, 112, .	2.5	26
47	Single-Alpha-Particle-Induced Charge Transient Spectroscopy of the 6H-SiC p^+n Diode Irradiated With High-Energy Electrons. IEEE Transactions on Nuclear Science, 2011, 58, 3328-3332.	2.0	4
48	Transient Analysis of an Extended Drift Region in a 6H-SiC Diode Formed by a Single Alpha Particle Strike and Its Contribution to the Increased Charge Collection. IEEE Transactions on Nuclear Science, 2011, 58, 305-313.	2.0	12
49	Oxygen Ion Induced Charge in SiC MOS Capacitors Irradiated with Gamma-Rays. Materials Science Forum, 2011, 679-680, 362-365.	0.3	2
50	Charge Enhancement Effects in 6H-SiC MOSFETs Induced by Heavy Ion Strike. IEEE Transactions on Nuclear Science, 2010, , .	2.0	6
51	Doping Concentration Optimization for Ultra-Low-Loss 4H-SiC Floating Junction Schottky Barrier Diode (Super-SBD). Materials Science Forum, 2009, 615-617, 655-658.	0.3	8
52	Charge Collection Properties of 6H-SiC Diodes by Wide Variety of Charged Particles up to Several Hundreds MeV. Materials Science Forum, 2009, 615-617, 861-864.	0.3	7
53	Evaluation of 4H-SiC Thermal Oxide Reliability Using Area-Scaling Method. Japanese Journal of Applied Physics, 2009, 48, 081404.	1.5	18
54	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). IEEE Transactions on Electron Devices, 2008, 55, 1954-1960.	3.0	30

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55	Characterization of Electrical Properties in SiC Crystals by Raman Scattering Spectroscopy. Materials Science Forum, 2008, 600-603, 501-504.	0.3	3
56	Effects of Fabrication Process on the Electrical Characteristics of n-Channel MOSFETs Irradiated with Gamma-Rays. Materials Science Forum, 2008, 600-603, 707-710.	0.3	1
57	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. Applied Physics Letters, 2008, 93, .	3.3	20
58	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaN/GaN HFET. Materials Science Forum, 2007, 556-557, 1043-1046.	0.3	1
59	Effect of Additional Silane on In Situ H ₂ Etching prior to 4H-SiC Homoepitaxial Growth. Materials Science Forum, 2007, 556-557, 85-88.	0.3	23
60	Simulation, Fabrication and Characterization of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). Materials Science Forum, 2007, 556-557, 881-884.	0.3	8
61	Decrease of Charge Collection Due to Displacement Damage by Gamma Rays in a 6H-SiC Diode. IEEE Transactions on Nuclear Science, 2007, 54, 1953-1960.	2.0	16
62	Influence of lattice polarity of nitrogen and aluminum doping on 4H-SiC epitaxial layer. Microelectronic Engineering, 2006, 83, 79-81.	2.4	11
63	Homoepitaxial Growth on a 4H-SiC C-Face Substrate. Chemical Vapor Deposition, 2006, 12, 489-494.	1.3	8
64	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. Materials Science Forum, 2006, 527-529, 147-152.	0.3	8
65	Fabrication of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs) and their Electrical Properties. Materials Science Forum, 2006, 527-529, 1175-1178.	0.3	12
66	High Inversion Channel Mobility of 4H-SiC MOSFETs Fabricated on C(000-1) Epitaxial Substrate with Vicinal (Below 1°) Off-Angle. Materials Science Forum, 2006, 527-529, 1043-1046.	0.3	8
67	Effect of Surface Orientation and Off-Angle on Surface Roughness and Electrical Properties of p-Type Impurity Implanted 4H-SiC Substrate after High Temperature Annealing. Materials Science Forum, 2006, 527-529, 835-838.	0.3	2
68	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. Applied Physics Letters, 2006, 89, 022909.	3.3	70
69	Nitrogen incorporation characteristics on a 4H-SiC epitaxial layer. Applied Physics Letters, 2006, 88, 021907.	3.3	12
70	Effect of growth condition on micropipe filling of 4H-SiC epitaxial layer. Journal of Crystal Growth, 2005, 275, e549-e554.	1.5	20
71	Modeling of SiC-CVD on Si-face/C-face in a horizontal hot-wall reactor. Journal of Crystal Growth, 2005, 275, e515-e520.	1.5	12
72	Epitaxial Overgrowth of 4H-SiC for Devices with p-Buried Floating Junction Structure. Materials Science Forum, 2005, 483-485, 147-150.	0.3	3

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73	2-Inch 4H-SiC Homoepitaxial Layer Grown on On-Axis C-Face Substrate by CVD Method. Materials Science Forum, 2005, 483-485, 93-96.	0.3	7
74	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. Materials Science Forum, 2005, 483-485, 661-664.	0.3	20
75	Defect Characterization of 4H-SiC Bulk Crystals Grown on Micropipe Filled Seed Crystals. Materials Science Forum, 2005, 483-485, 315-318.	0.3	0
76	Lifetime Control of the Minority Carrier in PiN Diodes by He ⁺ Ion Implantation. Materials Science Forum, 2005, 483-485, 985-988.	0.3	3
77	Impact ionization coefficients of 4H silicon carbide. Applied Physics Letters, 2004, 85, 1380-1382.	3.3	115
78	Reverse characteristics of pn diodes on 4H-SiC(000-1) C and (11-20) face. Applied Physics Letters, 2004, 84, 1774-1776.	3.3	11
79	Effects of n-type 4H-SiC epitaxial wafer quality on reliability of thermal oxides. Applied Physics Letters, 2004, 85, 6182-6184.	3.3	15
80	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. Journal of Applied Physics, 2004, 96, 2708-2715.	2.5	79
81	Effect of gate oxidation method on electrical properties of metal-oxide-semiconductor field-effect transistors fabricated on 4H-SiC C(0001 ₀₀) face. Applied Physics Letters, 2004, 84, 2088-2090.	3.3	141
82	Impact Ionization Coefficients of 4H-SiC. Materials Science Forum, 2004, 457-460, 673-676.	0.3	7
83	4H-SiC Carbon-Face Epitaxial Layers Grown by Low-Pressure Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 2004, 457-460, 209-212.	0.3	2
84	Relationship between the Current Direction in the Inversion Layer and the Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors on 3C-SiC. Materials Science Forum, 2004, 457-460, 1405-1408.	0.3	2
85	A Long-Term Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. Materials Science Forum, 2004, 457-460, 1269-1274.	0.3	4
86	Electrical Properties of pn Diodes on 4H-SiC(000-1) C-Face and (11-20) Face. Materials Science Forum, 2004, 457-460, 1065-1068.	0.3	3
87	4H-SiC MOSFETs on C(000-,1) Face with Inversion Channel Mobility of 127cm ² /Vs. Materials Science Forum, 2004, 457-460, 1417-1420.	0.3	21
88	Direct observation of dislocations propagated from 4H-SiC substrate to epitaxial layer by X-ray topography. Journal of Crystal Growth, 2004, 260, 209-216.	1.5	182
89	Influence of growth conditions on basal plane dislocation in 4H-SiC epitaxial layer. Journal of Crystal Growth, 2004, 271, 1-7.	1.5	88
90	Homoepitaxial growth of 4H-SiC on on-axis C-face substrates by chemical vapor depositon. Journal of Crystal Growth, 2004, 269, 367-376.	1.5	56

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91	Influence of C/Si Ratio on the 4H-SiC (0001) Epitaxial Growth and a Keynote for High-Rate Growth. Materials Science Forum, 2004, 457-460, 213-216.	0.3	14
92	Uniformity of 4H-SiC epitaxial layers grown on 3-in diameter substrates. Journal of Crystal Growth, 2003, 258, 113-122.	1.5	6
93	N-channel MOSFETs fabricated on homoepitaxy-grown 3C-SiC films. IEEE Electron Device Letters, 2003, 24, 466-468.	3.9	39
94	Epitaxial Growth of High-Quality 4H-SiC Carbon-Face by Low-Pressure Hot-Wall Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, L637-L639.	1.5	66
95	The Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors Fabricated on Cubic Silicon Carbide. Japanese Journal of Applied Physics, 2003, 42, L625-L627.	1.5	35
96	Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. Materials Science Forum, 2002, 389-393, 195-198.	0.3	5
97	A Large Reduction in Interface-State Density for MOS Capacitor on 4H-SiC (11-2 0) Face Using H ₂ and H ₂ O Vapor Atmosphere Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1057-1060.	0.3	6
98	Replication of Defects from 4H-SiC Wafer to Epitaxial Layer. Materials Science Forum, 2002, 389-393, 447-450.	0.3	5
99	Significant Improvement of Inversion Channel Mobility in 4H-SiC MOSFET on (11-20) Face Using Hydrogen Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1061-1064.	0.3	11
100	Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. Materials Science Forum, 2002, 389-393, 1053-1056.	0.3	1
101	High-Rate Epitaxial Growth of 4H-SiC Using a Vertical-Type, Quasi-Hot-Wall CVD Reactor. Materials Science Forum, 2002, 389-393, 179-182.	0.3	14
102	Distribution Profile of Deep Levels in SiC Observed by Isothermal Capacitance Transient Spectroscopy. Materials Science Forum, 2002, 389-393, 851-854.	0.3	0
103	Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 2002, 389-393, 215-218.	0.3	8
104	Influence of stacking faults on the performance of 4H-SiC Schottky barrier diodes fabricated on (112 ₁ ,0) face. Applied Physics Letters, 2002, 81, 2974-2976.	3.3	27
105	Excellent effects of hydrogen postoxidation annealing on inversion channel mobility of 4H-SiC MOSFET fabricated on (11 2 0) face. IEEE Electron Device Letters, 2002, 23, 13-15.	3.9	94
106	Control of Surface Morphologies for Epitaxial Growth on Low Off-Angle 4H-SiC (0001) Substrates. Materials Science Forum, 2001, 353-356, 135-138.	0.3	4
107	Effects of Pyrogenic Reoxidation Annealing on Inversion Channel Mobility of 4H-SiC Metal-Oxide-Semiconductor Field-Effect Transistor Fabricated on (112 ₁ ,0) Face. Japanese Journal of Applied Physics, 2001, 40, L1201-L1203.	1.5	10
108	Effects of Steam Annealing on Electrical Characteristics of 3C-SiC Metal-Oxide-Semiconductor Structures. Materials Science Forum, 2000, 338-342, 1129-1132.	0.3	0

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109	Transient Response to High Energy Heavy Ions in 6H-SiC n ⁺ /p Diodes. Materials Science Forum, 0, 600-603, 1039-1042.	0.3	1
110	Gate-Area Dependence of SiC Thermal Oxides Reliability. Materials Science Forum, 0, 600-603, 787-790.	0.3	3
111	Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance. Materials Science Forum, 0, 600-603, 907-912.	0.3	0
112	Transient Currents Induced in 6H-SiC MOS Capacitors by Oxygen Ion Incidence. Materials Science Forum, 0, 615-617, 517-520.	0.3	5
113	Control of the Surface Morphology on Low Off Angled 4H-SiC Homoepitaxial Growth. Materials Science Forum, 0, 615-617, 113-116.	0.3	9
114	Isotropic Channel Mobility in UMOSFETs on 4H-SiC C-Face with Vicinal Off-Angle. Materials Science Forum, 0, 645-648, 999-1004.	0.3	24
115	4H-SiC Homoepitaxial Growth on Vicinal-Off Angled Si-Face Substrate. Materials Science Forum, 0, 645-648, 99-102.	0.3	8
116	Charge Collection Efficiency of 6H-SiC P ⁺ /N Diodes Degraded by Low-Energy Electron Irradiation. Materials Science Forum, 0, 645-648, 921-924.	0.3	7
117	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. Materials Science Forum, 0, 679-680, 8-11.	0.3	14
118	Improvement of Homoepitaxial Layer Quality Grown on 4H-SiC ₀₀₁ Si-Face Substrate Lower than 1 Degree Off Angle. Materials Science Forum, 0, 717-720, 141-144.	0.3	6
119	Peak Degradation of Heavy-Ion Induced Transient Currents in 6H-SiC MOS Capacitors. Materials Science Forum, 0, 717-720, 469-472.	0.3	1
120	Effect of Post-Oxidation Annealing in Wet O ₂ and N ₂ O Ambient on Thermally Grown SiO ₂ /4H-SiC Interface for P-Channel MOS Devices. Materials Science Forum, 0, 717-720, 709-712.	0.3	8
121	Defects in an Electron-Irradiated 6H-SiC Diode Studied by Alpha Particle Induced Charge Transient Spectroscopy: Their Impact on the Degraded Charge Collection Efficiency. Materials Science Forum, 0, 717-720, 267-270.	0.3	0
122	Challenges of High-Performance and High-Reliability in SiC MOS Structures. Materials Science Forum, 0, 717-720, 703-708.	0.3	21
123	The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. Materials Science Forum, 0, 740-742, 193-196.	0.3	7
124	Development of SiC Super-Junction (SJ) Device by Deep Trench-Filling Epitaxial Growth. Materials Science Forum, 0, 740-742, 785-788.	0.3	27
125	Filling of Deep Trench by Epitaxial SiC Growth. Materials Science Forum, 0, 740-742, 793-796.	0.3	17
126	Low Resistivity, Thick Heavily Al-Doped 4H-SiC Epilayers Grown by Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 0, 740-742, 181-184.	0.3	22

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127	Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. Materials Science Forum, 0, 778-780, 135-138.	0.3	11
128	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. Materials Science Forum, 0, 778-780, 99-102.	0.3	4
129	Analysis on Generation of Localized Step-Bunchings on 4H-SiC(0001)Si Face by Synchrotron X-Ray Topography. Materials Science Forum, 0, 778-780, 398-401.	0.3	17
130	Carrier Density Dependence of Fano Type Interference in Raman Spectra of p-type 4H-SiC. Materials Science Forum, 0, 778-780, 475-478.	0.3	9
131	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. Materials Science Forum, 0, 778-780, 370-373.	0.3	19
132	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. Materials Science Forum, 0, 778-780, 109-112.	0.3	4
133	Development of SiC Super-Junction (SJ) Devices by Multi-Epitaxial Growth. Materials Science Forum, 0, 778-780, 845-850.	0.3	23
134	Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces. Materials Science Forum, 0, 778-780, 521-524.	0.3	15